

ABSTRACT OF THE DISCLOSURE

5 A chemical vapor deposition (CVD) method for depositing a silicide and a CVD system for performing the same are disclosed. A silicide is deposited on a substrate. Residual gases remaining from the depositing step are purged out by flowing air including H_2O (g), to substantially remove fumes caused by the residual gases. In the purge step, the cycle purge is carried out at the conditions similar to the flow of atmosphere, to substantially remove the fumes.

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